

ABSTRACT OF DISCLOSURE

A thin film transistor includes a one conductive type semiconductor layer (11); a source region (12) and a drain region (13) which are separately provided in the semiconductor layer; and a gate electrode (14) provided above or below the semiconductor layer with an insulating film interposed therebetween, wherein the width (W_s) of the junction face between the source region and the channel (16) which is provided between the source region and drain region, is different from the width (W_d) of the junction face between the above channel region and the drain region.